

*81*  
*Amended*  
irradiating an intense light to said insulating film; and  
forming a gate electrode on said insulating film.

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*92*  
6. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400°C.; and

*F*  
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

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*93*  
11. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas; and

forming a gate electrode on said insulating film;

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Amended

introducing phosphorus into said first and second semiconductor islands; and  
introducing boron into said second semiconductor island,  
wherein a dose amount of said boron is larger than that of said phosphorus.

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94

30. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film over a substrate;  
patterning the crystallized semiconductor film to form first and second semiconductor islands; F

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;

irradiating an intense light to said insulating film;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

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95

34. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film over a substrate;  
patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;

irradiating an intense light to said insulating film in an atmosphere comprising an